



# 《风光欣》技术资料

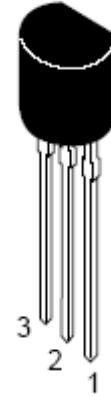
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## 2SC1008

### NPN EPITAXIAL SILICON TRANSISTOR

#### ABSOLUTE MAXIMUM RATINGS(TA=25 )

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V <sub>CBO</sub>	80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	60	V
Emitter -Base Voltage	V <sub>EBO</sub>	8	V
Collector Current	I <sub>c</sub>	700	mA
Collector Dissipation	P <sub>c</sub>	700	mW
Junction Temperature	T <sub>J</sub>	150	
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	



- 1. Emitter
- 2. Base
- 3. Collector

#### ELECTRICAL CHARACTERISTICS(T<sub>A</sub>=25 )

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	I <sub>c</sub> = 0.1mA, I <sub>E</sub> =0	80			V
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>c</sub> = 1mA, I <sub>B</sub> =0	60			V
Emitter -Base Breakdown Voltage	BV <sub>EBO</sub>	I <sub>E</sub> = 0.1mA, I <sub>C</sub> =0	8			V
Collector Cut-off Current	I <sub>CBO</sub>	V <sub>CB</sub> = 60V, I <sub>E</sub> =0			100	nA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> = 5V, I <sub>C</sub> =0,			100	nA
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> = 500mA, I <sub>B</sub> =50mA		0.2	0.5	V
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = 2V, I <sub>c</sub> =50mA,	40		400	
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 10V, I <sub>c</sub> = 50mA	30	50		MHZ
Output Capacitance	C <sub>OB</sub>	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f=1MHZ		8		pF

#### h<sub>FE</sub> CLASSIFICATION

Ltem	R	O	Y	G
H <sub>FE</sub>	40-80	70-140	120-240	200-400